MJD31C and MJD32C are Preferred Devices

## **Complementary Power Transistors**

#### **DPAK For Surface Mount Applications**

Designed for general purpose amplifier and low speed switching applications.

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Lead Formed Version in 16 mm Tape and Reel ("T4" Suffix)
- Electrically Similar to Popular TIP31 and TIP32 Series

#### **MAXIMUM RATINGS**

Rating	Symbol	MJD31 MJD32	MJD31C MJD32C	Unit
Collector–Emitter Voltage	V <sub>CEO</sub>	40	100	Vdc
Collector–Base Voltage	V <sub>CB</sub>	40	100	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5		Vdc
Collector Current - Continuous Peak	IC	3 5		Adc
Base Current	I <sub>B</sub>	1		Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	15 0.12		Watts W/°C
Total Power Dissipation (Note 1)  @ T <sub>A</sub> = 25°C  Derate above 25°C	P <sub>D</sub>	1.56 0.012		Watts W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150		°C

These ratings are applicable when surface mounted on the minimum pad size recommended



http://onsemi.com

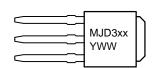
SILICON
POWER TRANSISTORS
3 AMPERES
40 AND 100 VOLTS
15 WATTS











STRAIGHT LEADS CASE 369 STYLE 1

MJD3xx = Specific Device Code

xx = 1, 1C, 2 or 2C Y = Year

WW = Work Week

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	8.3	°C/W
Thermal Resistance, Junction to Ambient (Note 2)	$R_{ heta JA}$	80	°C/W
Lead Temperature for Soldering Purposes	TL	260	°C

<sup>2.</sup> These ratings are applicable when surface mounted on the minimum pad size recommended.

#### **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (Note 3) $(I_C = 30 \text{ mAdc}, I_B = 0)$	MJD31, MJD32 MJD31C, MJD32C	V <sub>CEO(sus)</sub>	40 100	_ _	Vdc
Collector Cutoff Current ( $V_{CE} = 40 \text{ Vdc}, I_{B} = 0$ ) ( $V_{CE} = 60 \text{ Vdc}, I_{B} = 0$ )	MJD31, MJD32 MJD31C, MJD32C	I <sub>CEO</sub>	-	50	μAdc
Collector Cutoff Current $(V_{CE} = Rated V_{CEO}, V_{EB} = 0)$		ICES	-	20	μAdc
Emitter Cutoff Current $(V_{BE} = 5 \text{ Vdc}, I_C = 0)$		I <sub>EBO</sub>	_	1	mAdc
ON CHARACTERISTICS (Note 3)					
DC Current Gain ( $I_C = 1 \text{ Adc}, V_{CE} = 4 \text{ Vdc}$ ) ( $I_C = 3 \text{ Adc}, V_{CE} = 4 \text{ Vdc}$ )		h <sub>FE</sub>	25 10	_ 50	-
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 3 Adc, I <sub>B</sub> = 375 mAdc)		V <sub>CE(sat)</sub>	-	1.2	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 3 Adc, V <sub>CE</sub> = 4 Vdc)		V <sub>BE(on)</sub>	-	1.8	Vdc
DYNAMIC CHARACTERISTICS					
Current Gain – Bandwidth Product (Note 4) (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1 MHz)		f <sub>T</sub>	3	-	MHz
Small–Signal Current Gain (I <sub>C</sub> = 0.5 Adc, V <sub>CE</sub> = 10 Vdc, f = 1 kHz)		h <sub>fe</sub>	20	_	-

<sup>3.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2%. 4.  $f_T = |h_{fe}| \bullet f_{test}$ .

#### TYPICAL CHARACTERISTICS

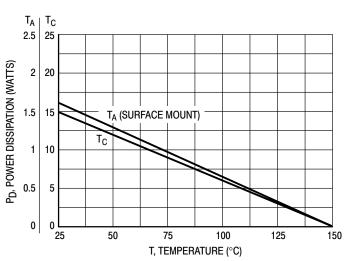
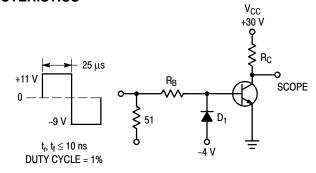


Figure 1. Power Derating



 $\rm R_B$  and  $\rm R_C$  VARIED TO OBTAIN DESIRED CURRENT LEVELS  $\rm D_1$  MUST BE FAST RECOVERY TYPE, e.g.: 1N5825 USED ABOVE  $\rm I_B\approx 100~mA$  MSD6100 USED BELOW  $\rm I_B\approx 100~mA$  REVERSE ALL POLARITIES FOR PNP.

Figure 2. Switching Time Test Circuit

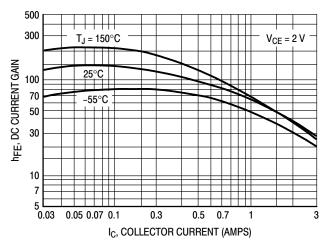


Figure 3. DC Current Gain

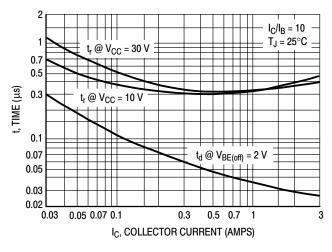


Figure 4. Turn-On Time

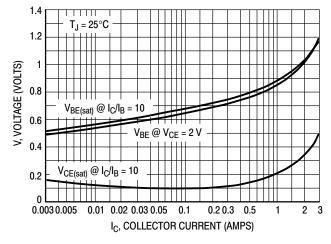


Figure 5. "On" Voltages

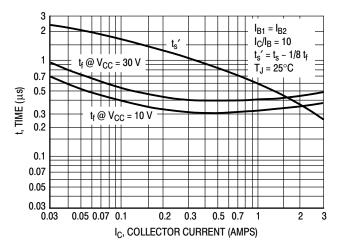
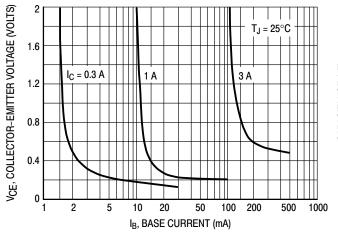


Figure 6. Turn-Off Time



300  $T_{.J} = +25^{\circ}C$ 200 CAPACITANCE (pF) 100 70 50  $C^{cp}$ 30 0.2 0.3 20 30 40 0.1 2 3 5 V<sub>R</sub>, REVERSE VOLTAGE (VOLTS)

Figure 7. Collector Saturation Region

Figure 8. Capacitance

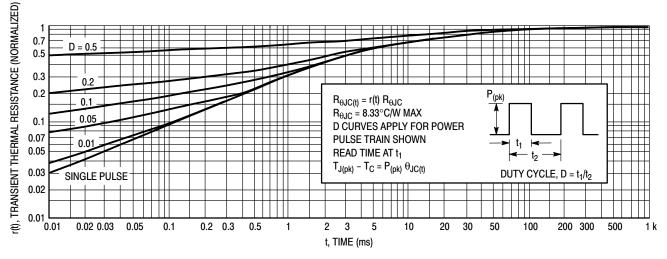


Figure 9. Thermal Response

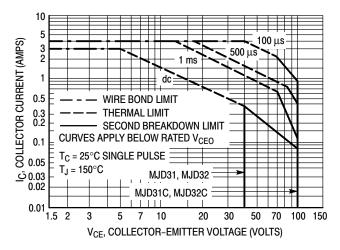
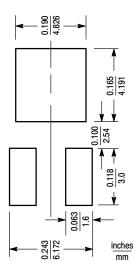


Figure 10. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 10 is based on  $T_{J(pk)} = 150$ °C;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150$ °C.  $T_{J(pk)}$  may be calculated from the data in Figure 9. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

#### MINIMUM PAD SIZES RECOMMENDED FOR SURFACE MOUNTED APPLICATIONS

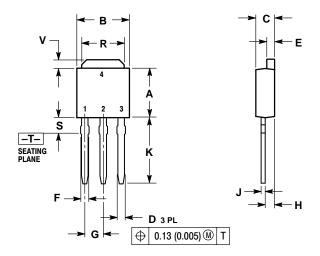


#### **ORDERING INFORMATION**

Device	Package	Shipping
MJD31C	DPAK	75 Units / Rail
MJD31CRL	DPAK	1800 Tape & Reel
MJD31CT4	DPAK	2500 Tape & Reel
MJD31C-1	DPAK Straight Leads	75 Units / Rail
MJD31T4	DPAK	2500 Tape & Reel
MJD32C	DPAK	75 Units / Rail
MJD32CRL	DPAK	1800 Tape & Reel
MJD32CT4	DPAK	2500 Tape & Reel
MJD32C-1	DPAK Straight Leads	75 Units / Rail
MJD32RL	DPAK	1800 Tape & Reel
MJD32T4	DPAK	2500 Tape & Reel

#### **PACKAGE DIMENSIONS**

**DPAK** CASE 369A-13 **ISSUE AA** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

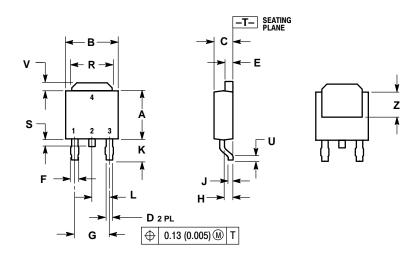
	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.250	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
Е	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.090 BSC		2.29 BSC	
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.175	0.215	4.45	5.46
S	0.050	0.090	1.27	2.28
V	0.030	0.050	0.77	1.27

STYLE 1:

- PIN 1. BASE 2. COLLECTOR 3. EMITTER

  - 4. COLLECTOR

#### **DPAK** CASE 369-07 ISSUE M



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.250	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.180	BSC	4.58 BSC	
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29	BSC
R	0.175	0.215	4.45	5.46
S	0.020	0.050	0.51	1.27
U	0.020		0.51	
٧	0.030	0.050	0.77	1.27
Z	0.138		3.51	

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

**Notes** 

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